

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a switching element formed on a semiconductor substrate, a first interconnect layer formed on the semiconductor substrate and having a first wiring connected to one terminal of the switching element, a ferroelectric capacitor formed on the first interconnect layer and having a first electrode connected to the one terminal of the switching element via the first wiring, a first protective film formed on the ferroelectric capacitor and the first interconnect layer, a second interconnect layer formed on the first protective film and having a second wiring connected to a second electrode of the ferroelectric capacitor and a first interlayer insulating film having a dielectric constant of 4 or more, and a third interconnect layer formed on the second interconnect layer and having a second interlayer insulating film with a dielectric constant of less than 4.